To all our customers

Regarding the change of names mentioned in the document, such as Hitachi Electric and Hitachi XX, to Renesas Technology Corp.

The semiconductor operations of Mitsubishi Electric and Hitachi were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Hitachi, Hitachi, Ltd., Hitachi Semiconductors, and other Hitachi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Renesas Technology Home Page: http://www.renesas.com

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.
Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corporation product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corporation or a third party.

2. Renesas Technology Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.

3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corporation without notice due to product improvements or other reasons.   It is therefore recommended that customers contact Renesas Technology Corporation or an authorized Renesas Technology Corporation product distributor for the latest product information before purchasing a product listed herein.
The information described here may contain technical inaccuracies or typographical errors.
Renesas Technology Corporation assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.
Please also pay attention to information published by Renesas Technology Corporation by various means, including the Renesas Technology Corporation Semiconductor home page (http://www.renesas.com).

4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products.   Renesas Technology Corporation assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.

5. Renesas Technology Corporation semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake.   Please contact Renesas Technology Corporation or an authorized Renesas Technology Corporation product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.

6. The prior written approval of Renesas Technology Corporation is necessary to reprint or reproduce in whole or in part these materials.

7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.
Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.

8. Please contact Renesas Technology Corporation for further details on these materials or the products contained therein.

HD49815TF

Digital Camera Signal Processor

RENESAS

Description

The HD49815TF is a CMOS IC that has been developed as a digital signal-processing IC for CCD-camera digital-signal-processing systems.

Functions

- CCD-sensor drive-pulse generation (TG)
- Digital AGC (automatic gain control)
- Color signal separation circuit
- RGB matrix
- RGB gain
- RGB and Y gamma
- Color-difference matrix
- Enhancer
- RGB and Y setup
- Digital I/F (4:2:2)
- Zoom control
- Mirror reversal
- Synchronization signal generator for encoding (SSG)
- AWB, AE, and AF detection
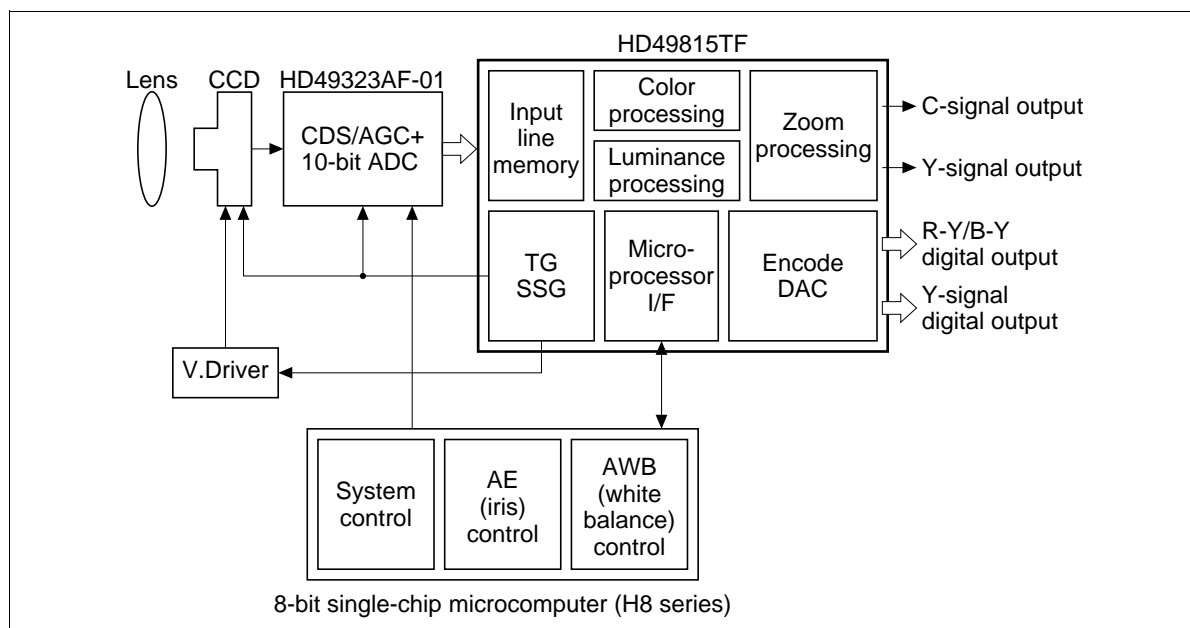- Two-channel 8-bit D/A converter

Features

- The HD49815TF provides camera-signal processing, TG, SSG, zoom, and D/A functions and other functions in a single chip and supports high system-integration level.
- In conjunction with the HD49323AF-01 (CDS/AGC + 10-bit ADC) and the control microcomputer, the HD49815TF forms a three-chip kit that can implement an optimal CCD-camera digital-signal-processing system.
- The HD49815TF provides the zoom function and controls the 1- to 256- times linear zoom. It also provides the half-mirror function.
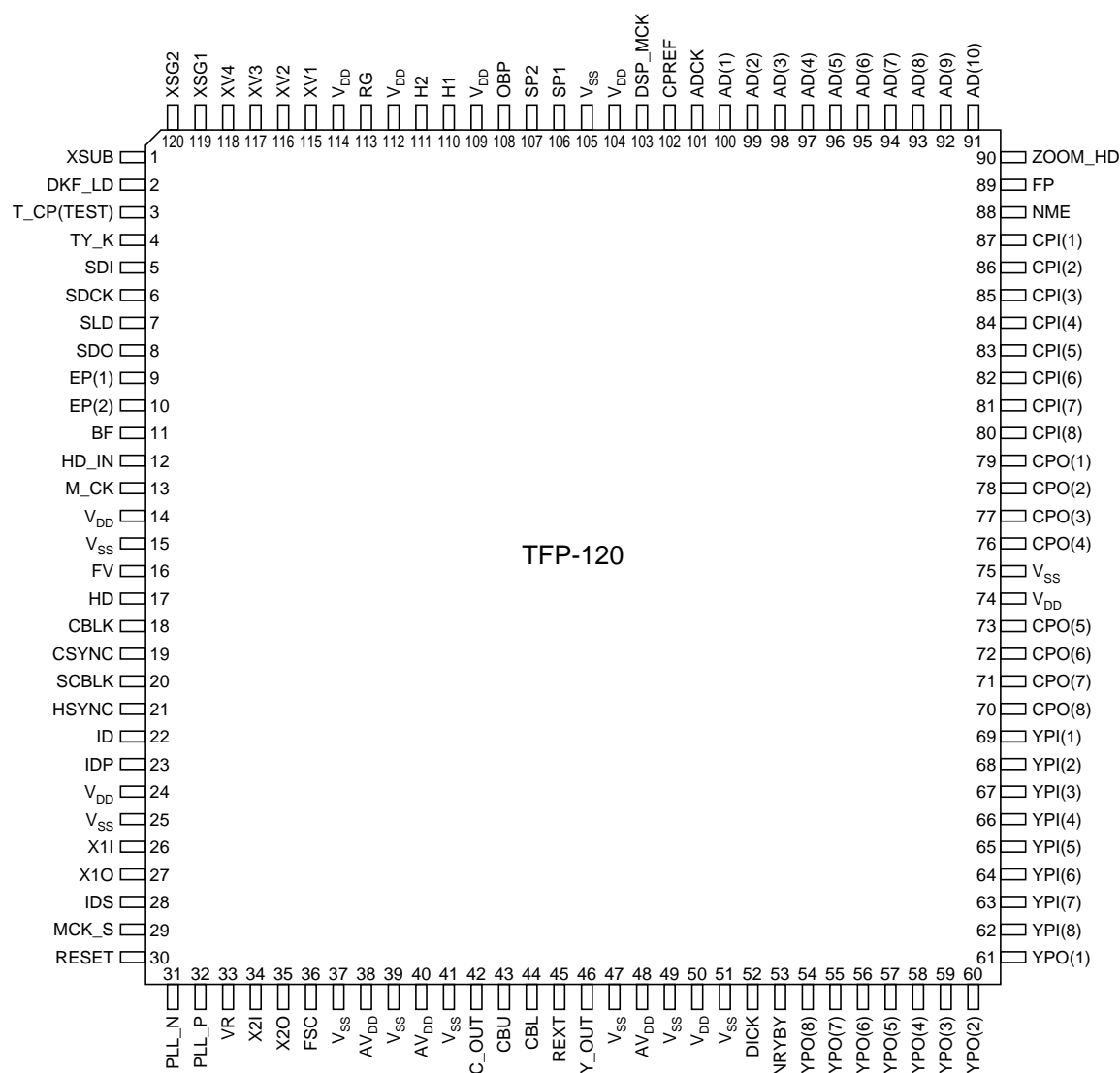
HD49815TF

Features (cont)

- Since the HD49815TF can be made compatible with the former product, HD49811TFA, through software, a shorter development term is enabled.
- Since software controls AWB, AE, and AF, any protocol can be prepared according to the camera shooting conditions.
- Programmable TG enables use of any CCD device.

System Block Diagram

Pin Arrangement

Top pins (left to right, 120–91): XSG2, XSG1, XV4, XV3, XV2, XV1, V_{DD}, RG, V_{DD}, H2, H1, V_{DD}, OBP, SP2, SP1, V_{SS}, V_{DD}, DSP_MCK, CPREF, ADCK, AD(1), AD(2), AD(3), AD(4), AD(5), AD(6), AD(7), AD(8), AD(9), AD(10)

Left pins (top to bottom, 1–30):
1 XSUB
2 DKF_LD
3 T_CP(TEST)
4 TY_K
5 SDI
6 SDCK
7 SLD
8 SDO
9 EP(1)
10 EP(2)
11 BF
12 HD_IN
13 M_CK
14 V_{DD}
15 V_{SS}
16 FV
17 HD
18 CBLK
19 CSYNC
20 SCBLK
21 HSYNC
22 ID
23 IDP
24 V_{DD}
25 V_{SS}
26 X1I
27 X1O
28 IDS
29 MCK_S
30 RESET

TFP-120

(Top view)

Right pins (top to bottom, 90–61):
90 ZOOM_HD
89 FP
88 NME
87 CPI(1)
86 CPI(2)
85 CPI(3)
84 CPI(4)
83 CPI(5)
82 CPI(6)
81 CPI(7)
80 CPI(8)
79 CPO(1)
78 CPO(2)
77 CPO(3)
76 CPO(4)
75 V_{SS}
74 V_{DD}
73 CPO(5)
72 CPO(6)
71 CPO(7)
70 CPO(8)
69 YPI(1)
68 YPI(2)
67 YPI(3)
66 YPI(4)
65 YPI(5)
64 YPI(6)
63 YPI(7)
62 YPI(8)
61 YPO(1)

Bottom pins (left to right, 31–60): PLL_N, PLL_P, VR, X2I, X2O, FSC, V_{SS}, AV_{DD}, V_{SS}, AV_{DD}, V_{SS}, C_OUT, CBU, CBL, REXT, Y_OUT, V_{SS}, AV_{DD}, V_{SS}, V_{DD}, V_{SS}, DICK, NRYBY, YPO(8), YPO(7), YPO(6), YPO(5), YPO(4), YPO(3), YPO(2)

Pin Description

Pin No.	Symbol	Pin Name	I/O	Description	I/O Format
1	XSUB	CCD shutter pulse	O	CCD control pulse	ZC2R
2	DKF_LD	Line input LD	I	Line input dedicated load	ICS
3	T_CP	Test	I	Test pin (GND input)	IC
4	TY_K	Title SW	I	Title-killer SW (1 = On, 0 = Off)	ICD
5	SDI	State data input	I	State data-setting data input	IC
6	SDCK	State data clock	I	State data-setting clock	ICS
7	SLD	State data load pulse	I	State data-latch pulse	ICS
8	SDO	AWB, AE, data output	O	AWB, AE, and AF detection-data output	ZC2R
9	EP (1)	AE window pulse 1	O	Iris detection-area-setting pulse: SP-A7 [8] output changeover	ICZC2R
10	EP (2)	AE window pulse 2	O	Iris detection-area-setting pulse: SP-A7 [8] output changeover	ICZC2R
11	BF	Burst flag	O	Burst flag output	ICZC2R
12	HD_IN	External CSYNC input	I	External CSYNC input	ICSD
13	M_CK	Microprocessor clock	O	Microprocessor clock output (1/2 or 1/4 dividing of X'tal 1)	OC2R
14	V_{DD}	$V_{CC}2$	—	3.3 V power supply	VCCI
15	V_{SS}	GND	—	GND	GNDI
16	FV	Field vertical output	O	Vertical synchronization pulse	ICZC2R
17	HD	HD output	O	Horizontal synchronization pulse	ICZC2R
18	CBLK	Blanking pulse	O	Blanking pulse	ICZC2R
19	CSYNC	SYNC output	O	SYNC pulse	ICZC2R
20	SCBLK	SC blanking pulse	O	Subcarrier blanking pulse (SECAM)	ICZC2R
21	HSYNC	Horizontal SYNC	O	Horizontal SYNC pulse (SECAM)	OC2R
22	ID	Identity	O	SECAM determination pulse	OC2R
23	IDP	Identity pulse	O	SECAM determination pulse	ICZC2R
24	V_{DD}	$V_{CC}2$	—	3.3 V power supply	VCCC
25	V_{SS}	GND	—	GND	GNDC
26	X1I	X'tal 1 input	I	2fsc oscillator input	IQ3
27	X1O	X'tal 1 output	O	2fsc oscillator output	OQ3
28	IDS	Line ID reset input	I	Line-determination-signal input	ICD
29	MCK_S	MCK output SW	I	Pin 13 MCK dividing setting SW (1 = 1/2, 0 = 1/4)	IC
30	RESET	Reset	I	Reset: to restore the initial data settings	ICS

RENESAS

4

Pin Description (cont)

Pin No.	Symbol	Pin Name	I/O	Description	I/O Format
31	PLL_N	PLL negative	O	PLL signal output	ZC2
32	PLL_P	PLL positive	O	PLL signal output	ZC2
33	VR	Vertical reset	I	Vertical synchronization signal input	ICSD
34	X2I	X'tal 2 input	I	4fsc oscillator input	IQ2
35	X2O	X'tal 2 output	O	4fsc oscillator output	OQ2
36	FSC	Sub carrier frequency	O	fsc output	ICZC2R
37	V_{SS}	GND	—	GND	GNDA
38	AV_{DD}	Analog $V_{CC}2$	—	Analog system power supply: 3.3 V	VCCA
39	V_{SS}	GND	—	GND	GNDA
40	AV_{DD}	Analog $V_{CC}2$	—	Analog system power supply: 3.3 V	VCCA
41	V_{SS}	GND	—	GND	GNDA
42	C_OUT	C analog signal output	O	Chrominance-signal analog output	OA
43	CBU	Current buffer upper	I	D/A upper current source	IA
44	CBL	Current buffer lower	I	D/A lower current source	IA
45	REXT	Reference resister EXT	I	Reference voltage input	IA
46	Y_OUT	Y analog signal output	O	Luminance-signal analog output	OA
47	V_{SS}	GND	—	GND	GNDA
48	AV_{DD}	Analog $V_{CC}2$	—	Analog system power supply: 3.3 V	VCCA
49	V_{SS}	GND	—	GND	GNDA
50	V_{DD}	$V_{CC}2$	—	Digital system power supply: 3.3 V	VCCI
51	V_{SS}	GND	—	GND	GNDI
52	DICK	Digital interface clock	O	Digital interface clock output	ICZC2R
53	NRYBY	R-Y, B-Y phase output	O	Color-difference signal phase clock	ICZC2R
54	YPO (8)	Y parallel output (8); MSB	O	Luminance-signal digital output MSB	OC2R
55	YPO (7)	Y parallel output (7)	O	Luminance-signal digital output	OC2R
56	YPO (6)	Y parallel output (6)	O	Luminance-signal digital output	OC2R
57	YPO (5)	Y parallel output (5)	O	Luminance-signal digital output	OC2R
58	YPO (4)	Y parallel output (4)	O	Luminance-signal digital output	OC2R
59	YPO (3)	Y parallel output (3)	O	Luminance-signal digital output	OC2R
60	YPO (2)	Y parallel output (2)	O	Luminance-signal digital output	OC2R
61	YPO (1)	Y parallel output (1) ; LSB	O	Luminance-signal digital output LSB	OC2R
62	YPI (8)	Y parallel input (8); MSB	I	Luminance-signal digital input MSB	ICD
63	YPI (7)	Y parallel input (7)	I	Luminance-signal digital input	ICD
64	YPI (6)	Y parallel input (6)	I	Luminance-signal digital input	ICD

RENESAS

Pin Description (cont)

Pin No.	Symbol	Pin Name	I/O	Description	I/O Format
65	YPI (5)	Y parallel input (5)	I	Luminance-signal digital input	ICD
66	YPI (4)	Y parallel input (4)	I	Luminance-signal digital input	ICD
67	YPI (3)	Y parallel input (3)	I	Luminance-signal digital input	ICD
68	YPI (2)	Y parallel input (2)	I	Luminance-signal digital input	ICD
69	YPI (1)	Y parallel input (1); LSB	I	Luminance-signal digital input LSB	ICD
70	CPO (8)	C parallel output (8); MSB	O	Chrominance-signal digital output MSB	OC2R
71	CPO (7)	C parallel output (7)	O	Chrominance-signal digital output	OC2R
72	CPO (6)	C parallel output (6)	O	Chrominance-signal digital output	OC2R
73	CPO (5)	C parallel output (5)	O	Chrominance-signal digital output	OC2R
74	V_{DD}	$V_{CC}2$	—	3.3 V power supply	VCCO
75	V_{SS}	GND	—	GND	GNDO
76	CPO (4)	C parallel output (4)	O	Chrominance-signal digital output	OC2R
77	CPO (3)	C parallel output (3)	O	Chrominance-signal digital output	OC2R
78	CPO (2)	C parallel output (2)	O	Chrominance-signal digital output	OC2R
79	CPO (1)	C parallel output (1); LSB	O	Chrominance-signal digital output LSB	OC2R
80	CPI (8)	C parallel input (8); MSB	I	Chrominance-signal digital input MSB	ICD
81	CPI (7)	C parallel input (7)	I	Chrominance-signal digital input	ICD
82	CPI (6)	C parallel input (6)	I	Chrominance-signal digital input	ICD
83	CPI (5)	C parallel input (5)	I	Chrominance-signal digital input	ICD
84	CPI (4)	C parallel input (4)	I	Chrominance-signal digital input	ICD
85	CPI (3)	C parallel input (3)	I	Chrominance-signal digital input	ICD
86	CPI (2)	C parallel input (2)	I	Chrominance-signal digital input	ICD
87	CPI (1)	C parallel input (1); LSB	I	Chrominance-signal digital input LSB	ICD
88	NME	Memory HD output	O	Line memory control output	ICZC2DR
89	FP	Field pulse	O	Field pulse	ICZC2R
90	ZOOM_HD	Zoom HD output	O	Horizontal synchronization signal	ICZC2R
91	AD (10)	AD input (10); MSB	I	A/D data input MSB	IC
92	AD (9)	AD input (9)	I	A/D data input	IC
93	AD (8)	AD input (8)	I	A/D data input	IC
94	AD (7)	AD input (7)	I	A/D data input	IC

RENESAS

Pin Description (cont)

Pin No.	Symbol	Pin Name	I/O	Description	I/O Format
95	AD (6)	AD input (6)	I	A/D data input	IC
96	AD (5)	AD input (5)	I	A/D data input	IC
97	AD (4)	AD input (4)	I	A/D data input	IC
98	AD (3)	AD input (3)	I	A/D data input	IC
99	AD (2)	AD input (2)	I	A/D data input	IC
100	AD (1)	AD input (1); LSB	I	A/D data input LSB	IC
101	ADCK	AD clock	O	A/D converter clock	ICZC2R
102	CPREF	Clamp reference output	O	Clamp reference pulse	2C3
103	DSP_MCK	Microprocessor clock output	O	Microprocessor clock output: SP-A7 [8] output changeover	ICZC2R
104	V_{DD}	$V_{CC}2$	—	3.3 V power supply	VCCO
105	V_{SS}	GND	—	GND	GNDO
106	SP1	Sampling pulse 1	O	Sampling pulse for the AGC/CDS IC	ICZC2
107	SP2	Sampling pulse 2	O	Sampling pulse for the AGC/CDS IC	ICZC2
108	OBP	OBP pulse	O	Optical black-pulse output	ICZC2R
109	V_{DD}	$V_{CC}1$	—	3 V or 5 V power supply (H1/H2 power supply)	VCCC35
110	H1	H1	O	CCD-sensor horizontal drive pulse	OC3R
111	H2	H2	O	CCD-sensor horizontal drive pulse	OC3R
112	V_{DD}	$V_{CC}1$	—	5 V power supply (RG power supply)	VCCC5
113	RG	Reset gate	O	CCD-sensor control reset gate	ZC3R
114	V_{DD}	$V_{CC}2$	—	3.3 V power supply	VCCO
115	XV1	XV1	O	CCD-sensor vertical control pulse	ICZC2R
116	XV2	XV2	O	CCD-sensor vertical control pulse	ICZC2R
117	XV3	XV3	O	CCD-sensor vertical control pulse	ICZC2R
118	XV4	XV4	O	CCD-sensor vertical control pulse	ICZC2R
119	XSG1	XSG1	O	CCD-sensor vertical control pulse	ZC2R
120	XSG2	XSG2	O	CCD-sensor vertical control pulse	ZC2R

Description of I/O Format

I/O Format	Contents
IC	CMOS level input
ICD	CMOS level input with pull-down resistor
ICS	CMOS level schmitt input
ICSD	CMOS level input with pull-down resistor
ICZC2	CMOS level common I/O (4 mA)
ICZC2DR	CMOS level common I/O with pull-down resistor and through-put control (4 mA)
ICZC2R	CMOS level common I/O with through-put control (4 mA)
OC2R	CMOS level output with through-put control (4 mA)
OC3R	CMOS level output with through-put control (8 mA)
IQ2	Crystal oscillator input
OQ2	Crystal oscillator output
IQ3	Crystal oscillator input
OQ3	Crystal oscillator output
ZC2	CMOS-level three-state output (4 mA)
ZC2R	CMOS-level three-state output with through-put control (4 mA)
ZC3	CMOS-level three-state output (8 mA)
ZC3R	CMOS-level three-state output with through-put control (8 mA)
VCCI	Core system power supply: 3 V
VCCO	Puddling system power supply: 3 V
VCCC	Common power supply: 3 V
VCCC5	Common power supply: 5 V for pin 112
VCCC35	Common power supply: 3 or 5 V for pin 109
GNDI	Core system GND
GNDO	Puddling system GND
GNDC	Common GND
IA	Analog input
OA	Analog output
VCCA	Analog power supply
GNDA	Analog GND

Notes: 1. Pin 113 is used for 5 V system output.
2. Pins 110 and 111 are used for 3 V or 5 V system output. They depend on the voltage of pin 109.
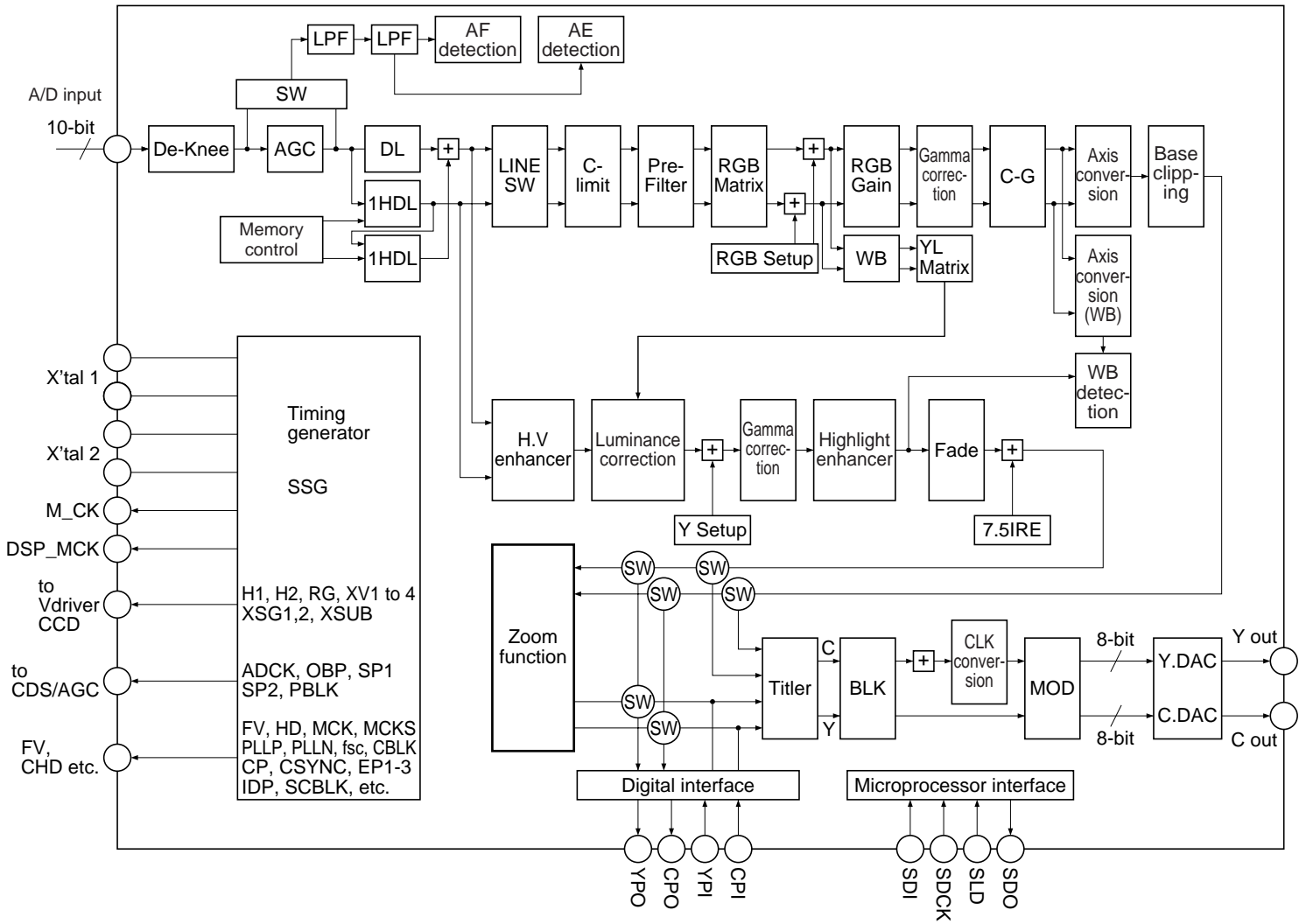
Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Power supply voltage		V_{CC}	–0.2 to +6.8	V
Pin voltage (5 V operation block)		Vt5V	–0.2 to V_{CC}1 +0.2	V
Pin voltage (3 V operation block)		Vt3V	–0.2 to V_{CC}2 +0.2	V
Output current	Per output	Io	–32 to +32	mA
	Per GND-V_{CC} pair	Iot	–72 to +72	mA
Allowable power dissipation		Popr	450	mW
Operating temperature		Topr	–10 to +75	°C
Storage temperature	With bias	Tbias	–10 to +75	°C
	Without bias	Tstg	–40 to +125	°C

Notes: 1. Using this LSI at values in excess of the absolute maximum ratings may permanently damage the LSI. The LSI should normally be operated under the conditions specified for the electrical characteristics. Exceeding these conditions may lead to incorrect operation and may adversely affect LSI reliability.

2. All voltage values are referenced to GND = 0 V.

3. The pin voltage ratings also apply to the NC pins.

4. V_{CC}1 indicates the 5 V system power supply and V_{CC}2 indicates the 3 V system power supply.

RENESAS

Electrical Characteristics ($V_{CC}1$ = 4.75 V to 5.25 V, $V_{CC}2$ = 2.85 V to 3.15 V, AV_{CC} = 2.85 V to 3.15 V, Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions	Note
CMOS-level	V_{IHC}	$V_{CC}2{\times}0.75$	—	$V_{CC}2$	V		
input voltage	V_{ILC}	0.0	—	$V_{CC}2{\times}0.20$	V		
CMOS schmitt	$V_{TC}+$	2.50	—	$V_{CC}2$	V	$V_{CC}1$ = 5 V	
input voltage	$V_{TC}-$	0.0	—	0.60	V	$V_{CC}2$ = 3 V	
Output voltage	V_{OHC1}	$V_{CC}1{-}0.5$	—	—	V	I_{OH} = −200 μA 5 V system pin	1
	V_{OLC1}	—	—	0.4	V	I_{OL} = 200 μA 5 V system pin	
	V_{OHC2}	$V_{CC}2{-}0.5$	—	—	V	I_{OH} = −200 μA 3 V system pin	1, 5
	V_{OLC2}	—	—	0.4	V	I_{OL} = 200 μA 3 V system pin	1, 6
Input leakage current	I_{LI}	—	—	1.0	μA	V_{IN} = 0 V to V_{CC}	2
Output leakage current	I_{LO}	—	—	1.0	μA	Output Hi-Z conditions	2
Pull-down current	I_{PD}	5	—	100	μA	V_{IN} = $V_{CC}2$ = 3 V	
Power dissipation	Popr	—	—	450	mW	$V_{CC}1$ = 5 V, $V_{CC}2$ = 3 V, AV_{CC} = 3 V	3
Analog output voltage (full scale)	Vfull	0.80	1.00	1.20	V		3, 4
Analog output voltage (zero scale)	Vzero	−0.20	0.00	0.20	V		
Differential linearity	DNL	−2.0	—	2.0	LSB		

Notes: 1. Output voltage must be measured in the steady state.

2. Except for pins that include a pull-down resistor.

3. Guaranteed at CBU = 0.1 μF, CBL = 0.1 μF, REXT = 3.4 kΩ, analog output load resistance = 500 Ω, and Ta = 25°C.

4. Applied to pins indicated as OA in the I/O format column of the pin-functions table.

5. Because V_{OH} of pin 31 cannot be measured logically, it was not tested.

6. Because V_{OL} of pin 32 cannot be measured logically, it was not tested.

7. $V_{CC}1$, $V_{CC}2$, and AV_{CC} indicate the 5 V system power supply, the 3 V system power supply, and the analog system power supply, respectively. V_{CC} indicates $V_{CC}1$, $V_{CC}2$, and AV_{CC}.

8. The voltage range of pin 109 (VCCC35) is V_{CC} = 2.85 V to 5.25 V.

Crystal Oscillation Circuit

1. Measuring conditions

   The oscillation frequency was measured under the following conditions.

   $V_{CC}1 = 5.0$ V
   $V_{CC}2 = 3$ V
   Ta = 25°C
   8 MHz, 20 MHz, and 24 MHz:
       Rf = 1 to 10 MΩ
       Cin, Cout = 20 pF (±20 pF)
   32 MHz:
       Rf = 1 to 10 MΩ
       Cin = 20 pF (±20 pF)
       Cout = 100 pF (±20 pF), Co = 15 pF (±5 pF), Lout = 1 µH
   The conditions above may be changed within the range of measuring conditions.

2. Measuring method

   Under the measuring conditions above, two methods were tested.
   fmin. = 20 MHz, and fmax. = 32 MHz (applied to pins 26 and 27)
   fmin. = 8 MHz, and fmax. = 24 MHz (applied to pins 34 and 35)
   Note: The oscillation start time tosc is max. = 200 ms.

3. Measuring circuit
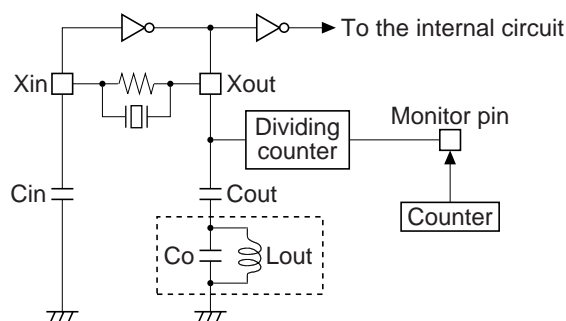
Note: The part enclosed by the dotted line in the above
circuit is used when measuring at 32 MHz.

Figure 1   Measuring Circuit

Built-in Functions and System Configuration

System Configuration
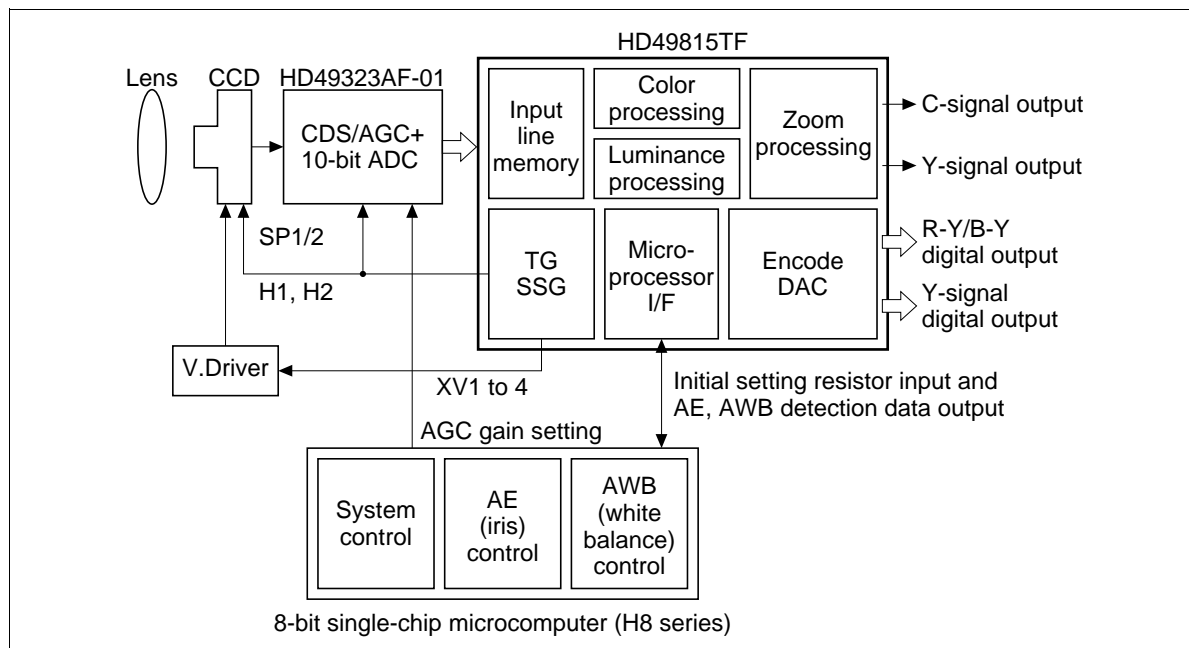
Figure 2   System Configuration

System Description

1. CCD

    The following lists the pixels of the CCD sensors that can be used with the HD49815TF. For other
    pixel numbers, contact our sales dept.

    512 (H) × 492 (V) NTSC

    512 (H) × 582 (V) PAL

    682 (H) × 492 (V) NTSC

    681 (H) × 582 (V) PAL

2. CDS/AGC + 10-bit ADC

    The HD49323AF-01 (manufactured by Hitachi) is recommended as an optimal CDS/AGC + 10-bit
    ADC IC for the HD49815TF. Since the HD49323AF-01 provides a correlated double sampling circuit
    that realizes high S/N and an automatic gain control (AGC) circuit that implements programmable
    control of 0 dB to 34.7 dB, it enables a high-image-quality camera system when used in conjunction
    with the HD49815TF.

3. 8-bit single-chip microcomputer

The 8-bit single-chip microcomputer controls the system. It receives the image detection data that the HD49815TF is gathering and implements automatic iris control (AE), automatic white balance control (AWB), and automatic focus control (AF).

When setting the power on, this microcomputer implements the initial setting to the state data of the HD49815TF.

For details on the state data, see "Hitachi Camera DSP (HD49815TF) State Data".

Built-in Functions

1. Input line memory block
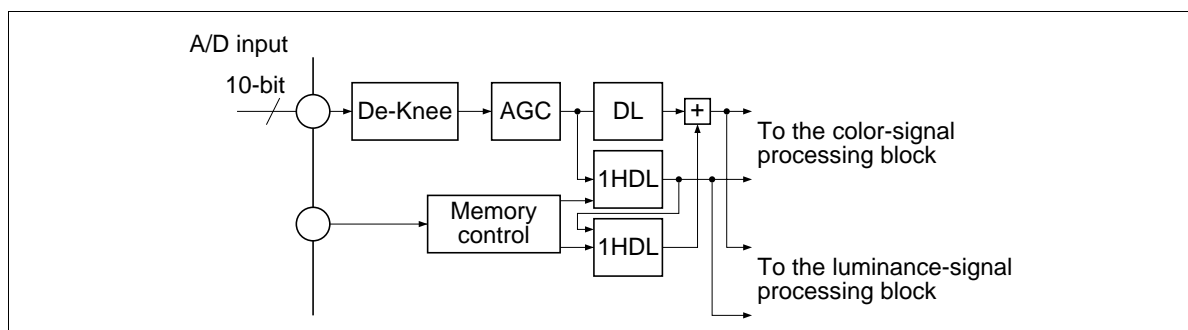
Figure 3   Input Line Memory Block

a. De-knee function

When the CDS/AGC IC at the pre-stage or the external circuit uses the knee circuit to expand the dynamic range of the signal, the de-knee (inverse knee) circuit returns the signal converted by the knee circuit to the original state.

The de-knee point can be set in State Data SP_A0 [1]. The gain of the high-luminance block is 1/2.

b. AGC function

A digital AGC circuit is provided. The AGC gain can be set in State Data SP_A0 [2] from 1 to 16 times.

c. 1H delay line (1HDL) function

This circuit obtains horizontal efficient pixels of the CCD output signal. The number of efficient pixels is set in State Data SP_A0 [9, 10] and TM_A0 [14] MCSET.

RENESAS

2. Color-signal processing block
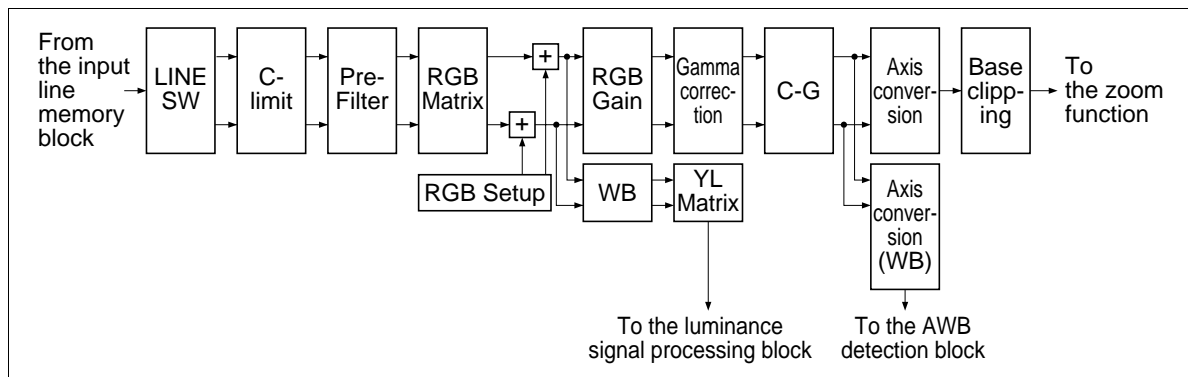
Figure 4   Color-Signal Processing Block

a. C-limit (complementary color clipping level) function

High clipping processing is performed on the complementary color signals independently. High clipping is set in State Data SP_A2 [0 to 3].

The complementary color signal indicates Gb: $(G + Cy)$, Wr: $(Ye + Mg)$, Wb: $(Mg + Cy)$, and Gr: $(G + Ye)$.

b. RGB-matrix block

The three primary colors (red, green, and blue) are acquired in the RGB matrix by multiplying arbitrary coefficients by the four complementary colors (Gb, Wr, Wb, and Gr) and taking the total of those results. The RGB matrix is designed to support the minimum color moire and to enable free color reproduction. Arbitrary coefficients are set in State Data SP_A2 [4 to 15]. The following shows the formula.

$$\begin{pmatrix} R \\ B \\ G \end{pmatrix} = \begin{bmatrix} KRa & KRb & KRc & KRd \\ KBa & KBb & KBc & KBd \\ KGa & KGb & KGc & KGd \end{bmatrix} \begin{pmatrix} Gb \\ Wr \\ Wb \\ Gr \end{pmatrix}$$

State Data SP_A2 [4 to 15]

c. RGB-setup block

The black level of the color signals is variable according to the coefficients of the RGB matrix. The value calculated by the formula below is subtracted from the color signal to correct the black level. The subtracted value can be set externally and is set in State Data SP_A3 [0 to 2].

Formula = $-[48 \times \Sigma \text{ (Matrix data)} \times 2^3]$

d. RGB-gain block

The RGB gain value acquired in the AWB control is set in the RGB gain circuit to improve the white reproduction performance. As it is set prior to the gamma correction, it changes the gamma correction amount. The RGB gain can be set in State Data SP_A3 [3 to 5] from 1 to 256 times. (The G gain is set from 1 to 128 times.)

RENESAS

e. C gamma (γ) correction block

The C gamma correction circuit performs gamma processing on the RGB signal. It is set in State Data SP_A3 [6 to 9]. Four kinds of values can be set independently, according to the input-signal level, to acquire optimal gamma characteristics: the C gamma dark (to reduce the gain of the small signals for improving S/N), C gamma coefficient (to control the expansion of the gamma curve), C gamma knee (to decide the slope of the large signals), and C gamma limit (to perform high-clipping processing for the input signal of the C gamma circuit).

f. YL matrix block

The luminance level changes according to the color temperature of the imaged object. Set State Data SP_A5 [12, 13] for the luminance correction. To correct the luminance, create YL from the three primary colors (R, G, and B) and convert it to the luminance signal level. The YL matrix circuit creates the YL level from the RGB signal.

The YL matrix is set in State Data SP_A3 [11 to 13].

g. The axis-conversion (C-Y matrix) block

The C-Y (color-difference) matrix takes R-G and B-G as its input signals, and creates the R-Y and B-Y color-difference signals by setting coefficients for those inputs.

The axis-conversion (C-Y matrix) circuits are set in State Data SP_A8 [0 to 5].

h. Base-clipping block

Since base clipping is performed on the color-difference signals, the base-clipping circuit has the characteristics of clipping the sections near axes on a vector scope.

This circuit is set in State Data SP_A8 [8].

3. Luminance-signal-processing block
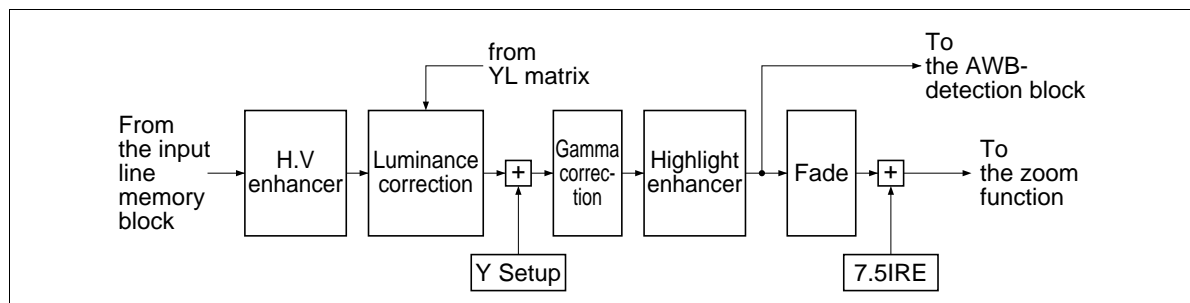
Figure 5   Luminance-Signal-Processing Block

a. H-enhancer function

The H-enhancer circuit allows the core level, the enhancer gain, and the noise coefficient to be set independently to acquire optimal characteristics.

This circuit is set in State Data SP_A4 [4 to 7].

b. V-enhancer function

The V-enhancer circuit allows the enhancer coefficient to be set and can control the gain for only those signal components that exceed the set core level.

This circuit is set in State Data SP_A4 [8 to 10].

RENESAS

c. Luminance correction

The ratio of the red and blue levels changes according to the color temperature of the imaged object. For example, if a red object is imaged at a low color temperature, the luminance level increases and the object appears to have a lower chrominance. Therefore, the luminance correction circuit performs luminance-correction processing to implement color depth reproduction.

The luminance-correction circuit is set in State Data SP_A5 [12, 13].

d. Y setup

Since the OB clamp processes the signal, the black level of the 10-bit signal input to the HD49815TF is fixed to 48/1024. The Y-setup circuit subtracts 48 at the black level. However, when 48 at the black level differs due to the noise mixed in the analog signal, the Y-setup circuit subtracts that value.

The Y-setup circuit is set in State Data SP_A5 [6].

e. Gamma correction

The gamma-correction circuit implements the gamma-correction processing for the separated Y signal. Four kinds of values can be set independently, according to the input-signal level, to acquire optimal gamma characteristics: the gamma input limit, the gamma knee coefficient, the gamma coefficient, and the gamma black clipping.

The gamma correction circuit is set in State Data SP_A5 [1 to 4].

f. Highlight enhancer

For input-Y signal levels in excess of 100 IRE, the highlight enhancer implements highlight enhancer processing.

This circuit is set in State Data SP_A5 [0, 5, and 14].

g. Fade

The fade circuit amplifies the luminance signal by a factor of 0 to 1.

This circuit is set in State Data SP_A5 [9].

4. Zoom, encode block, TG, SSG, and AWB and AE detection blocks

a. Zoom processing

The Y, R-Y, and B-Y signals completed the color-signal processing and the luminance-signal processing can be electronically zoomed by a factor of 1 to 256.

After clipping CCD signals for V direction, zoom circuit clips these signals for H direction, and expand these signals for H and V directions.

The zooming times and the read starting position for the V and H directions are set in State Data TM_A2 [3, 4, 5, 6, 8, and 9] and ZM_A0 to 6.

b. Encode block

This circuit encodes the signals completed the color-signal processing, the luminance-signal processing, and the zoom processing as the NTSC/PAL TV-monitor method.

A DAC that converts the digital signal to an analog signal is provided. The DAC has two channels: one for R-Y signals and one for B-Y signals.

c. TG and SSG

The TG generates the signals required to drive the CCD sensor (H1, H2, RG, SG1/2, and the V transfer pulse), and the CDS/AGC control signals (SP1 and SP2).

In addition, the SSG generates the signals to synchronize with the TV monitor (the Sync signal).

The drive timing of the generated signals differs according to the manufacturer and the specifications of the CCD sensor. Setting the state data enables setting of any timing.

The state data of TG and SSG can be set in TM_A0, A1, A2, A3, and A8.

d. AWB- and AE-detection blocks

The HD49815TF provides automatic white-balance (AWB) and automatic-iris (AE) detection circuits that are indispensable for a camera.

The AWB-detection block takes the R-Y and B-Y color-difference signals completed the color-signal processing, and converts to the R-B and MG-G axes. The converted signals are sent to circuits for the white detection to obtain white signal components only, and the white-color difference value is detected. The 8-bit single-chip microcomputer acquires this detection data, and controls the R and B gains to produce the true white.

The State Data of the AWB detection is AWB_A0 and A8.

The AE-detection block divides the CCD output signal converted to digital by the 10-bit ADC to six arbitrary areas, and performs integration processing. This function enables detection of the lighting level of the image signal.

The 8-bit single-chip microcomputer acquires this detection data, and controls the accumulation amount (the shutter) of the CCD sensor or the iris motor of the lens to maintain the proper lighting.

The State Data of the AF detection is AE_A0 to A7 and A8.

Microcomputer Interface Specifications

• Write format

SLD (Pin 7)

SDCK (Pin 6)

SDI (Pin 5)

LSB ... MSB   LSB   MSB LSB   MSB

D1 D2 D3 D4 D5 D6 D7 D8   D1 D2 D3 D4 D5 D6 D7 D8 D1 D2 D3 D4 D5 D6 D7 D8

|← 1 byte →| |← Address →|← Function address →|
|← Data (N byte) →|← STAL →|← STAH →| (write address)
STD3-----STH2-----STD1

• Read format

SLD (Pin 7)

SDCK (Pin 6)

SDI (Pin 5)

LSB   MSB LSB   MSB

D1 D2 D3 D4 D5 D6 D7 D8 D1 D2 D3 D4 D5 D6 D7 D8

|←   1 byte or 2 byte   →|
|← STAL →|← STAH →|← Function address →|

SDO (Pin 8)   Hi-Z

LSB   MSB

Hi-Z
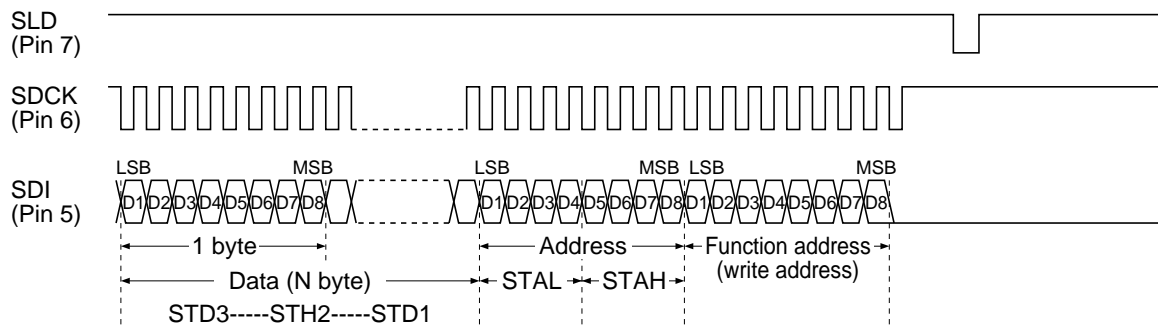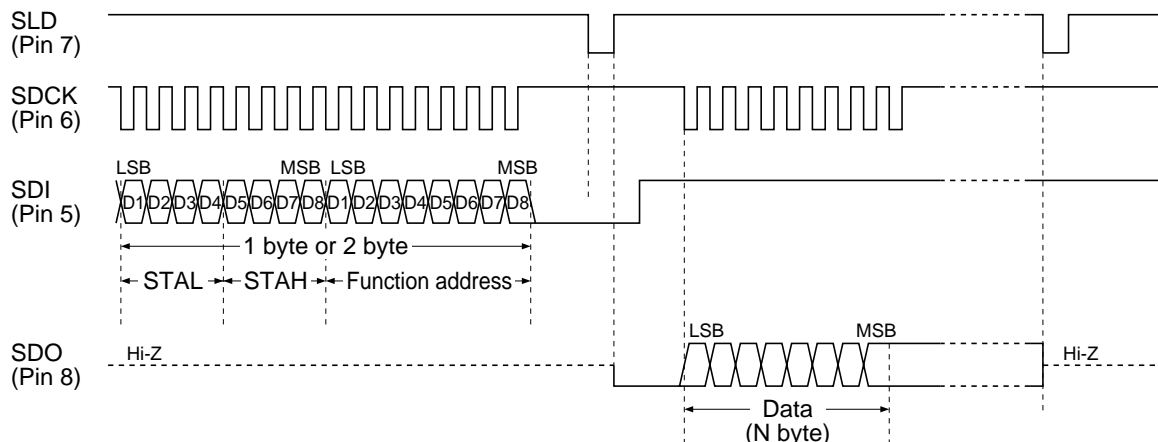
|← Data →|
(N byte)

Notes: 1. Synchronous serial transfer (The microcomputer serial port can be used.)
2. Transfer frequency: 3.58 MHz or lower
3. Data and address are handled in a byte unit.
4. The clock and load pulse are used in common for read/write.

RENESAS

Data Transfer Specification

For data transfer between the HD49815TF and the microcomputer, two types (N and E for write, and R1 and R2 for read) are available. The following table shows the relationship between the function block and the transfer specifications. On the next page, the details of the transfer specifications are described.

Function Block	Transfer Mode	Transfer Specifications *1	Related Address
Signal processing	W	N	SP_A0, 2 to 5, 7 to 10, 15
TM	W	N	TM_A3, 15
		E	TM_A0 to 2, 8, 10 to 12
	R	R1	TMR_A0
Iris	W	N	AE_A0 to 7
	R	R2	AE_A8
White balance	W	N	AWB_A0
	R	R1	AWB_A8
AF	W	N	AF_A0 to 3
	R	R1	AF_A8 to 13
ZOOM	W	N	ZM_A0 to 6

Note: 1. Transfer specifications

Type N   : Normal transfer from the microcomputer to the DSP
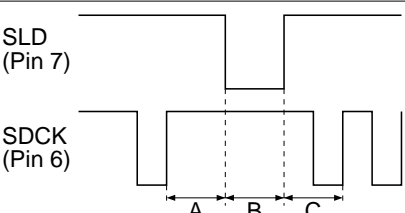
Type E   : Transfer using the set pulse (synchronous with VD) or the reset signal (used as a synchronous pulse in the DSP) sent from the microcomputer to the RS latch in the DSP

Note: This cannot be set during the standby mode.
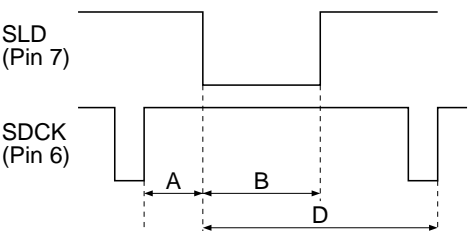
Type R1 : Data transfer (1) from the DSP to microcomputer

Type R2 : Data transfer (2) from the DSP to microcomputer

RENESAS
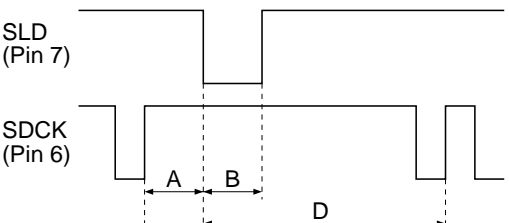
- Type N

Transfer specification	Pulse Timing	Conditions
N	SLD (Pin 7) / SDCK (Pin 6) A, B, C	A = 100 ns or more B = 100 ns or more C = 100 ns or more
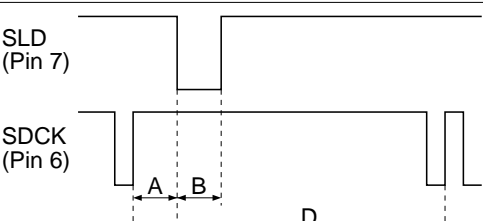
- Type E

Transfer specification	Pulse Timing	Conditions			
				270,000 pixels	410,000 pixels
E	SLD (Pin 7) / SDCK (Pin 6) A, B, D	A	0.5 / fs + 100 ns or more	150 ns or more	135 ns or more
		B	2 / fs + 100 ns or more	300 ns or more	240 ns or more
		D	5.5 / fs + 100 ns or more	650 ns or more	485 ns or more
		fs	Sensor clock	100 ns	70 ns

- Type R1

Transfer specification	Pulse Timing	Conditions
R1	SLD (Pin 7) / SDCK (Pin 6) A, B, D	A = 100 ns or more B = 100 ns or more D = 400 ns or more Do not read the white balance data and the AF read data within the 1H period from the start of the V blanking.

- Type R2

Transfer specification	Pulse Timing	Conditions			
R2	SLD (Pin 7) / SDCK (Pin 6) A, B, D	A = 100 ns or more B = 100 ns or more			
				270,000 pixels	410,000 pixels
		D	{1 / fs × (32 + 5) + 400 ns} or more	4.1 µs or more	2.99 µs or more
		fs	Sensor clock	100 ns	70 ns

HD49815TF

Note: 2 to 9. Function addresses

The following table shows the function addresses for each function block (during state data transfer) and the data to be transferred from the microcomputer.

Table 2 Function Addresses for each Function Block and State Data

		List of Data Transferred				Remarks

2 Signal processing (Setting example) — *This example is related to SP-A0[9].*

Function Address: `0 0 0 0 0 0 0 0` / `0 0 0 0 0 0 0 0`
STAH: `* * * * * * * *` / `0 0 0 0 1 0 0 1`
STAL: `* * * * * * * *` / `D8 D7 D6 D5 D4 D3 D2 D1`
STD1: `* * * * * * * *` / `—————————`
STD2: `* * * * * * * *` / `————————D9`

3 TM write (Setting example) — *This example is related to TM-A0 [14].*

Function Address: `0 0 0 0 0 0 0 1` / `0 0 0 0 0 0 0 1`
STAH: `* * * * * * * *` / `0 0 0 0 1 1 1 0`
STAL: `* * * * * * * *` / `D8 D7 D6 D5 D4 D3 D2 D1`
STD1: `* * * * * * * *` / `—————————`
STD2: `* * * * * * * *` / `—————————`

4 TM read

Function Address: `0 0 0 0 1 0 0 1`
Data read for automatic phase adjustment for SP1, SP2, and RG

5 AE W — *This example is related to the IRIS peak detection area.*

Function Address: `0 0 0 1 0` / `0 0 0 1 0 1 0 0`
ADATA: `* * *` / `—————`
STAH: `* * * * * * * *` / `—————D3 D2 D1`
STAL: `* * * * * * * *` / `—————————`
STD1: `————* * * *` / `—————————`
STD2: `0 0 0 0 0 0 0 0` / `0 0 0 0 0 0 0 0`

5 AE W — *This example is related to the window H count 3.*

Function Address: `0 0 0 0 0 0 0 1` / `0 0 0 0 0 0 0 1`
ADATA: `* * *` / `1 0 1`
STAH: `* * * * * * * *` / `0 0 0 1 0`
STAL: `* * * * * * * *` / `—————D5 D4 D3 D2 D1`
STD1: `————* * * *` / `—————————`
STD2: `0 0 0 0 0 0 0 0` / `0 0 0 0 0 0 0 0`

6 AE R

Function Address: `0 0 0 1 1 0 0 0`
STAH: `—————`
STAL: `* * * *`
Read area setting by STAL (4 bits)

7 AWB W — *This example is related to the offset R-B.*

Function Address: `0 0 1 0 0` / `0 0 1 0 0`
ADATA: `—————` / `—————`
STAH: `* * * * * * * *` / `0 0 0 0 1`
STAL: `* * * * * * * *` / `—————D6 D5 D4 D3 D2 D1`
STD1: `————* * * *` / `0 0 0 0 0 0 0 0`
STD2: `0 0 0 0 0 0 0 0` / `0 0 0 0 0 0 0 0`

7 AWB W — *This example is related to the V count 2.*

Function Address: `0 0 0 0 0 0 0 *` / `0 0 0 0 0 0 0 1`
ADATA: `* * *` / `1 0 1`
STAH: `* * * * * * * *` / `1 0 0 1 1`
STAL: `* * * * * * * *` / `D8 D7 D6 D5 D4 D3 D2 D1`
STD1: `————* * * *`
Window setting for white balance WB detection axis phase setting

8 AWB R

Function Address: `0 0 1 0 1 0 0 0`
White balance read

9 AF W — *This example is related to the HRF bandwidth selection.*

Function Address: `0 0 1 1 0` / `0 0 1 1 0 0 0 0`
ADATA: `* * *` / `—————`
STAH: `* * * * * * * *` / `————D4 D3 D2 D1`
HPF bandwidth selection, Base-clip quantity setting, etc.

9 AF W — *This example is related to the differential gate of V-end.*

Function Address: `0 0 0 0 0 0 0 1` / `0 0 0 0 0 0 0 1`
ADATA: `1 1 0` / `1 1 0`
STAH: `0 0 * * * * * *` / `0 0 1 0 1`
STAL: `* * * * * * * *` / `D8 D7 D6 D5 D4 D3 D2 D1`
STD1: Setting for integration and display gate

10 AF R

Function Address: `0 0 1 1 1 * * *`
Vf fetch address (read_cycle)

ZOOM W

Header: `1 0 1 1 0 * * *`
Data 1 | Data 2 | Data 3
Data 4 | Data 5 | Data 6

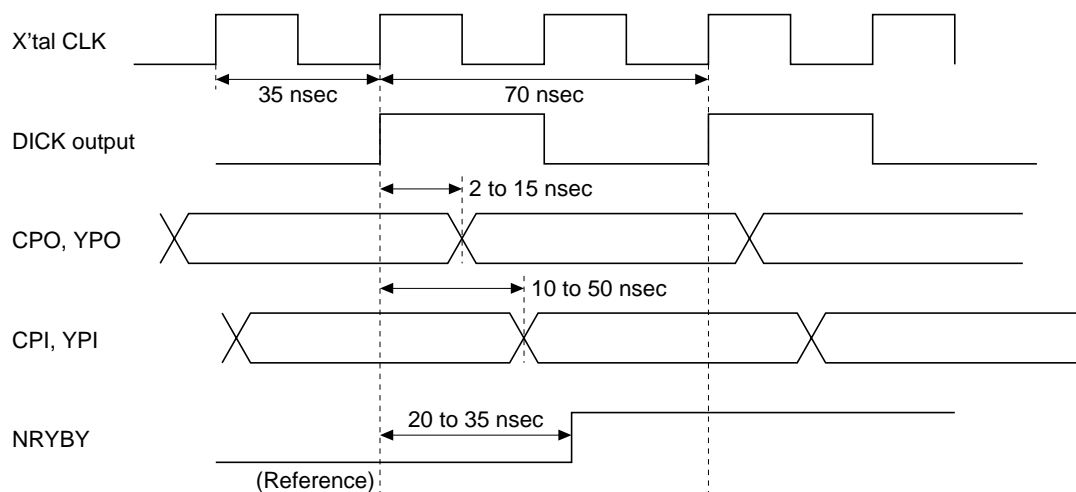Note: For the ZOOM, the transfer of in total of seven bytes is required for the header and data 1 to 6.

RENESAS

22

Digital Interface Timing

• The output specification and timing of the digital interface output (Y, R-Y, B-Y)

NRYBY

DICK

4 : 2 : 2 output timing

CPO (1 to 8)   〉〈 R-Y0 〉〈 B-Y0 〉〈 R-Y2 〉〈 B-Y1 〉〈 R-Y4 〉〈 B-Y4 〉〈 〉〈 〉〈 〉〈 〉

YPO (1 to 8)   〉〈 Y0 〉〈 Y1 〉〈 Y2 〉〈 Y3 〉〈 Y4 〉〈 Y5 〉〈 〉〈 〉〈 〉〈 〉
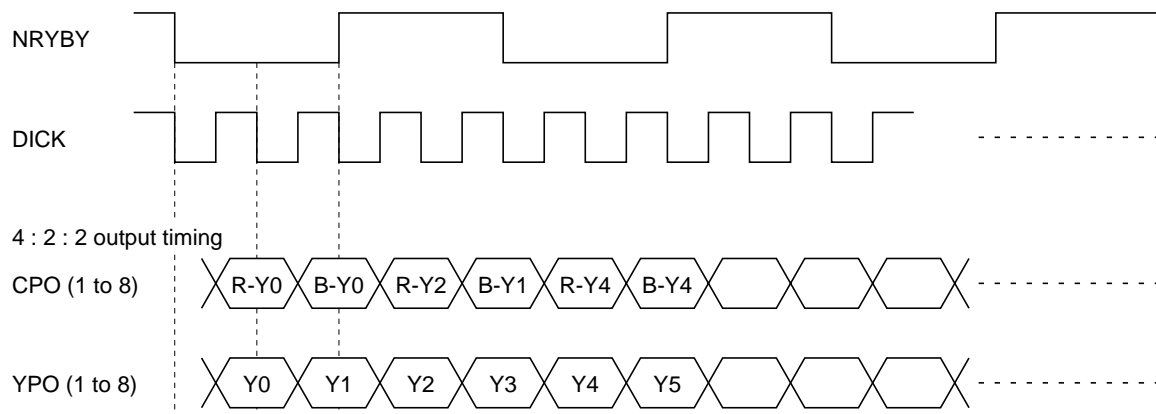
• Detailed specifications of digital interface timing

X'tal CLK

35 nsec   70 nsec

DICK output

2 to 15 nsec

CPO, YPO

10 to 50 nsec

CPI, YPI

20 to 35 nsec

NRYBY

(Reference)

NRYBY   : R-Y/B-Y determination pulse
DICK   : Clock dedicated to the digital interface (The clock generated from the external X'tal.)
CPO, YPO : Digital interface output terminal
CPI, YPI   : Digital interface input terminal

Package Dimensions

Unit: mm

16.0 ± 0.2

□14

90   61

91   60

16.0 ± 0.2

0.4

120   31

1   30

*0.17 ± 0.05
0.15 ± 0.04

⊕ 0.07 Ⓜ

1.2

1.00

1.20 Max

*0.17 ± 0.05
0.15 ± 0.04

0.10 ± 0.10

△ 0.10

1.0

0° − 8°

0.5 ± 0.1

*Dimension including the plating thickness
Base material dimension

Hitachi Code	TFP-120
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.5 g

RENESAS

Cautions

1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.

2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.

3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.

4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.

5. This product is not designed to be radiation resistant.

6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.

7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

RENESAS